- Low $r_{DS(on)} \dots 5 \Omega$ Typical
- Avalanche Energy . . . 30 mJ
- Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- Low Power Consumption

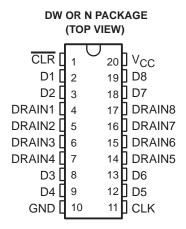
description

The TPIC6B273 is a monolithic, high-voltage, medium-current, power logic octal D-type latch with DMOS-transistor outputs designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

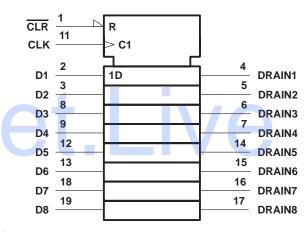
The TPIC6B273 contains eight positive-edgetriggered D-type flip-flops with a direct clear input. Each flip-flop features an open-drain power DMOS-transistor output.

When clear (CLR) is high, information at the D inputs meeting the setup time requirements is transferred to the DRAIN outputs on the positive-going edge of the clock (CLK) pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock input (CLK) is at either the high or low level, the D input signal has no effect at the output. An asynchronous CLR is provided to turn all eight DMOS-transistor outputs off. When data is low for a given output, the DMOS-transistor output is off. When data is high, the DMOS-transistor output has sink-current capability.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink-current capability. Each output provides a 500-mA typical current limit at $T_C = 25^{\circ}C$. The current limit decreases as the junction temperature increases for additional device protection.



logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12.

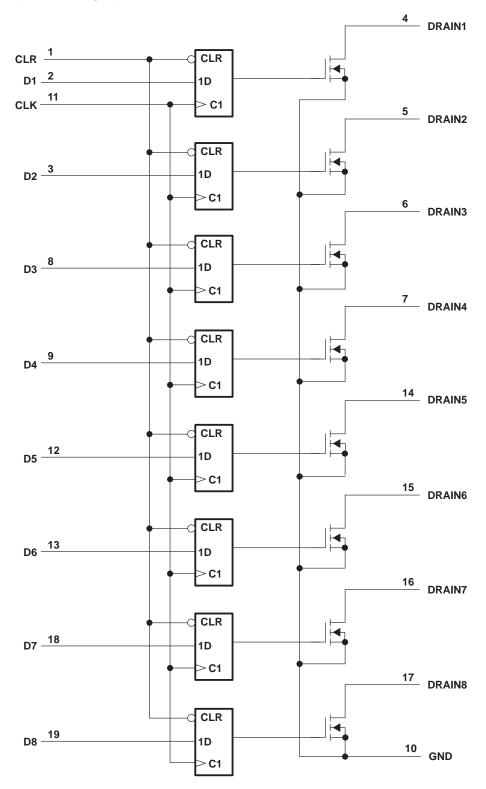
FUNCTION TABLE (each channel)

	INPUTS						
CLR	CLK	D	DRAIN				
L	Χ	Χ	Н				
Н	\uparrow	Н	L				
Н	\uparrow	L	Н				
Н	L	X	Latched				

H = high level, L = low level, X = irrelevant

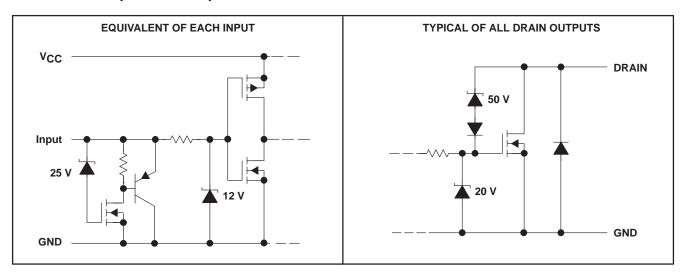
The TPIC6B273 is characterized for operation over the operating case temperature range of -40°C to 125°C.

logic diagram (positive logic)





schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) †

Logic supply voltage, V _{CC} (see Note 1)	7 V
Logic input voltage range, V _I	
Power DMOS drain-to-source voltage, V _{DS} (see Note 2)	
Continuous source-to-drain diode anode current	
Pulsed source-to-drain diode anode current (see Note 3)	1 A
Pulsed drain current, each output, all outputs on, I _D , T _C = 25°C (see Note 3)	500 mA
Continuous drain current, each output, all outputs on, I_D , $T_C = 25^{\circ}C$	150 mA
Peak drain current single output, I _{DM} ,T _C = 25°C (see Note 3)	500 mA
Single-pulse avalanche energy, E _{AS} (see Figure 4)	30 mJ
Avalanche current, I _{AS} (see Note 4)	500 mA
Continuous total dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T _J	40°C to 150°C
Operating case temperature range, T _C	40°C to 125°C
Storage temperature range	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to GND.
 - 2. Each power DMOS source is internally connected to GND.
 - 3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.
 - 4. DRAIN supply voltage = 15 V, starting junction temperature (TJS) = 25°C, L = 200 mH, IAS = 0.5 A (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T _C = 25°C	T _C = 125°C POWER RATING
DW	1389 mW	11.1 mW/°C	278 mW
N	1050 mW	10.5 mW/°C	263 mW



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recommended operating conditions

	MIN	MAX	UNIT
Logic supply voltage, V _{CC}	4.5	5.5	V
High-level input voltage, VIH	0.85 V _{CC}		V
Low-level input voltage, V _{IL}		0.15 V _{CC}	V
Pulsed drain output current, T _C = 25°C, V _{CC} = 5 V (see Notes 3 and 5)	-500	500	mA
Setup time, D high before CLK↑, t _{SU} (see Figure 2)	20		ns
Hold time, D high after CLK↑, th (see Figure 2)	20		ns
Pulse duration, t _W (see Figure 2)	40	·	ns
Operating case temperature, T _C	-40	125	°C

electrical characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$ (unless otherwise noted)

	PARAMETER		TEST CONDITION	ONS	MIN	TYP	MAX	UNIT
V(BR)DSX	Drain-to-source breakdown voltage	I _D = 1 mA			50			V
V _{SD}	Source-to-drain diode forward voltage	IF = 100 mA				0.85	1	V
lн	High-level input current	$V_{CC} = 5.5 \text{ V},$	$V_I = V_{CC}$				1	μΑ
I _I L	Low-level input current	$V_{CC} = 5.5 \text{ V},$	$V_I = 0$				-1	μΑ
l ania aumaha aumant		V _{CC} = 5.5 V	All outputs off			20	100	
ICC	ICC Logic supply current		All outputs on			150	300	μΑ
I _N	Nominal current	VDS(on) = 0.5 V, See Notes 5, 6, a	I _N = I _D , and 7	T _C = 85°C,		90		mA
1	Off-state drain current	$V_{DS} = 40 \text{ V},$	V _{CC} = 5.5 V			0.1	5	
IDSX	Oil-state drain current	V _{DS} = 40 V,	V _{CC} = 5.5 V,	T _C = 125°C		0.15	8	μΑ
		I _D = 100 mA,	V _{CC} = 4.5 V			4.2	5.7	
rDS(on)	Static drain-to-source on-state resistance	I _D = 100 mA, T _C = 125°C	V _{CC} = 4.5 V,	See Notes 5 and 6 and Figures 6 and 7		6.8	9.5	Ω
		$I_D = 350 \text{ mA},$	V _{CC} = 4.5 V	<u> </u>		5.5	8	

switching characteristics, V_{CC} = 5 V, T_{C} = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output from CLK			150		ns
tPHL	Propagation delay time, high-to-low-level output from CLK	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$		90		ns
t _r	Rise time, drain output	See Figures 1, 2, and 8		200		ns
t _f	Fall time, drain output			200		ns
ta	Reverse-recovery-current rise time	I _F = 100 mA, di/dt = 20 A/μs,		100		ns
t _{rr}	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		115

NOTES: 3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.

- 5. Technique should limit $T_J T_C$ to $10^{\circ}C$ maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- 7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_C = 85°C.



thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT	
Park	Thermal resistance investigate embient	DW package	All 8 outputs with equal power		90	°C/W
$R_{\theta JA}$	Thermal resistance, junction-to-ambient	N package	All 6 outputs with equal power		95	C/VV

PARAMETER MEASUREMENT INFORMATION

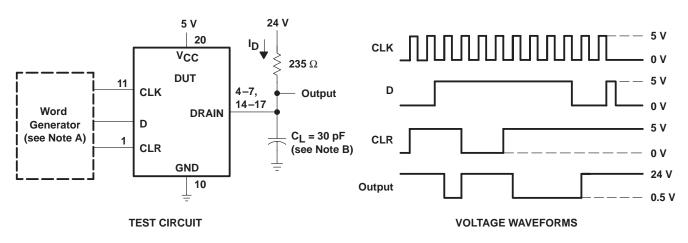


Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

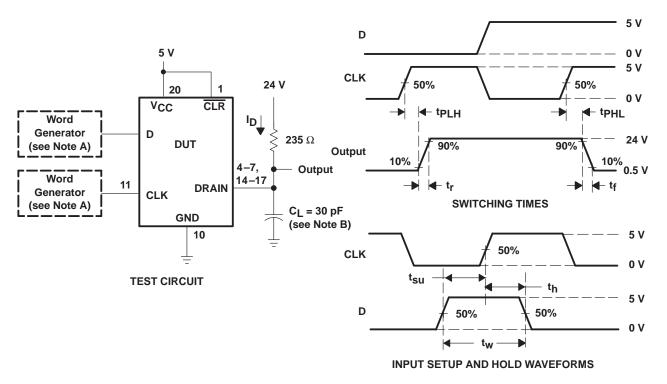


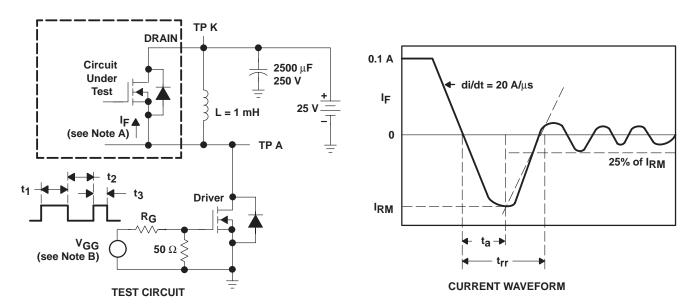
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

NOTES: A. The word generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $t_W = 300$ ns, pulsed repetition rate (PRR) = 5 KHz, $Z_O = 50 \ \Omega$.

B. C_L includes probe and jig capacitance.

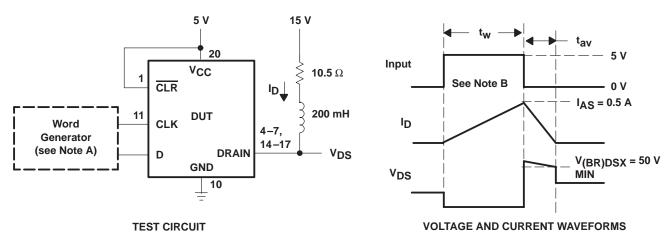


PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
 - B. The V_{GG} amplitude and R_{G} are adjusted for di/dt = 20 A/ μ s. A V_{GG} double-pulse train is used to set I_{F} = 0.1 A, where t_{1} = 10 μ s, t_{2} = 7 μ s, and t_{3} = 3 μ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



- NOTES: A. The word generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $Z_0 = 50 \ \Omega$.
 - B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 0.5$ A. Energy test is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30$ mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms



DRAIN-TO-SOURCE ON-STATE RESISTANCE

TYPICAL CHARACTERISTICS

PEAK AVALANCHE CURRENT VS TIME DURATION OF AVALANCHE 10 T_C = 25°C 4 0.4 0.2 0.1 0.1 0.1 0.2 0.4 1 2 4 10

Figure 5

tav - Time Duration of Avalanche - ms

DRAIN CURRENT To a state of the control of the con

Figure 6

300

400

ID - Drain Current - mA

500

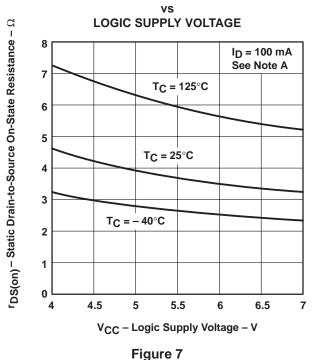
600

700

100

200

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE



NOTE C: Technique should limit T_J – T_C to 10°C maximum.

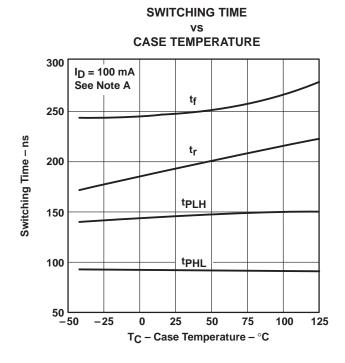


Figure 8



THERMAL INFORMATION

MAXIMUM CONTINUOUS DRAIN CURRENT OF EACH OUTPUT NUMBER OF OUTPUTS CONDUCTING **SIMULTANEOUSLY** 0.45 $V_{CC} = 5 V$ $I_D - Maximum Continuous Drain Current$ 0.4 0.35 0.3 of Each Output - A 0.25 T_C = 25°C 0.2 0.15 T_C = 100°C 0.1 T_C = 125°C 0.05 0 2 3 4 5 7 8 6 N - Number of Outputs Conducting Simultaneously

Figure 9

MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT NUMBER OF OUTPUTS CONDUCTING **SIMULTANEOUSLY** - Maximum Peak Drain Current of Each Output - A 0.5 d = 10%0.45 d = 20%0.4 0.35 d = 50%0.3 0.25 d = 80%0.2 0.15 $V_{CC} = 5 V$ $T_{C} = 25^{\circ}C$ 0.1 $d = t_W/t_{period}$ 0.05 = 1 ms/t_{period} ۵ 3 8 N - Number of Outputs Conducting Simultaneously

Figure 10





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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TPIC6B273DW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273DWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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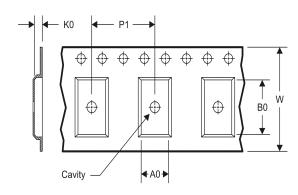
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6B273DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.1	2.65	12.0	24.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6B273DWR	SOIC	DW	20	2000	367.0	367.0	45.0

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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